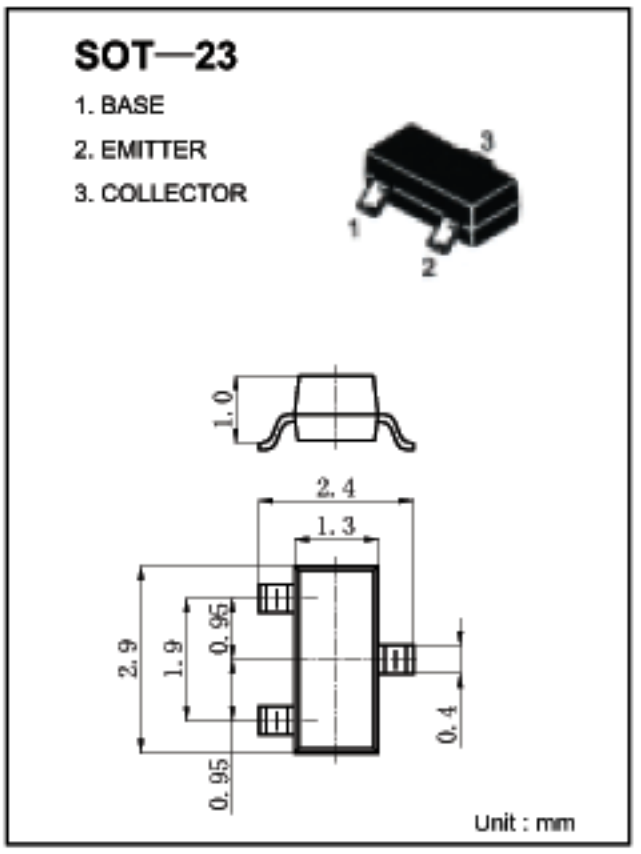
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO.,LTD

SOT-23 Plastic-Encapsulate Transistors

SS8550LT1 TRANSISTOR（ PNP ）



FEATURES

Power dissipation

P_{CM} : 0.625 W（Tamb=25℃）

Collector current

I_{CM} : -1.5 A

Collector-base voltage

$V_{(BR)CBO}$: -40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= -100 μA, I_E=0	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= -0.1mA, I_B=0	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100 μA, I_C=0	-6		V
Collector cut-off current	I_{CBO}	V_{CB}= -40 V, I_E=0		-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -20 V, I_B=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V, I_C=0		-0.1	μA
DC current gain	$H_{FE\ (1)}$	V_{CE}= -1V, I_C= -100mA	120	350	
	$H_{FE\ (2)}$	V_{CE}= -1V, I_C= -800mA	40		
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-800 mA, I_B= -80mA		-0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-800 mA, I_B= -80mA		-1.2	V
Base-emitter voltage	V_{BEF}	I_E=-1.5A		-1.6	V
Transition frequency	f_T	V_{CE}= -10V, I_C= -50mA f=30MHz	100		MHz

CLASSIFICATION OF $H_{FE(1)}$

Rank	L	H
Range	120-200	200-350

DEVICE MARKING

8550LT1=Y2